

## **Quarterly Reliability Monitoring Results**

## Quarters: Q1/2021 to Q4/2021

Based on structural similarity

Supplier Nexperia B.V.		User Part Number						
		BC850C						
Name of Laboratory		Part Description						
		Nexperia DHAM	Small Signal E	Bipolar Transist	or			
Assembly reliability labs		SMD package						
Based on AEC-Q101 Test		Test Conditions	Duration	# Lots	# Quantity	# Rejects		
	TEST							
	Pre- and Post-Stress							
# E1	Electrical Test	Tamb = 25 °C	N/A	see below	all parts	see below		
		JESD22-A113 Bake Tamb = 125 °C	24 hours					
	PC	Soak Tamb = 85 °C, RH = 85%	168 hours					
# A1	Preconditioning	Reflow soldering	3 cycles	849	61170	0		
		MIL-STD-750-1						
	HTRB	M1039 Method A						
" 54	High Temperature Reverse Bias	Tj = Tjmax, Vr = 100% of max. datasheet reverse voltage	1000	202	16160	•		
# B1	Dias	reverse voltage	1000 hours	202	16160	0		
	тс	JESD22-A104						
# A4	Temperature Cycling	-65 °C to Tjmax, not to exceed 150°C	1000 cycles	171	13680	0		
		JESD22-A102	,					
	AC	Tamb = 121 °C, RH = 100 %						
# A3 alt	Autoclave	Pressure = 205 kPa (29.7 psia)	96 hours	173	13840	0		
	H3TRB	JESD22-A101 Tamb = 85 °C, RH = 85%, VR = 80 % of						
# A2 alt	High Humidity High Temperature Reverse Bias		1000 hours	173	13840	0		
# AZ dIL	remperature Reverse Blus	MIL-STD-750 Method 1037	1000 110015	1/3	13640	U		
	IOL	ton = toff, devices powered to insure $\Delta T_j$ =						
# A5	Intermittent Operating Life		1000 hours	197	15760	0		
	RSH	JESD22-A111						
# C8	Resistance to Solder Heat	260 °C ± 5 °C	10 s	135	4050	0		
	SD Coldorobility	1 CTD 003						
# C10	Solderability	J-STD-002		342	3420	0		

<sup>[1]</sup> The maximum applied voltage is limited by test chamber set up and does not exceed 115V.

## **Calculation of FIT and MTTF**

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test #B1)
Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

Wafer Fab	Technology	Quantity	Rejects	Failure Rate (FIT)	MTTF (hrs)
Nexperia	Small Signal Bipolar				
DHAM	Transistor	16160	0	0.26	3.81E+09

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